TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MA157FK

Low Voltage Quad 2-Channel Multiplexer with 3.6 V Tolerant Inputs and Outputs

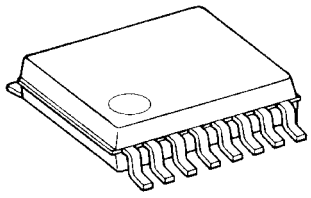
The TC7MA157FK is a high performance CMOS multiplexer which is guaranteed to operate from 1.2-V to 3.6-V. Designed for use in 1.5 V, 1.8 V, 2.5 V or 3.3 V systems, it achieves high. speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.

It consists of four 2-input digital multiplexers with common select and strobe inputs.

When the $\overline{ST}$ input is held "H" level, selection of data is inhibited and all the outputs become "L" level. The SELECT decoding determines whether the A or B inputs get routed to their corresponding Y outputs.

All inputs are equipped with protection circuits against static discharge.



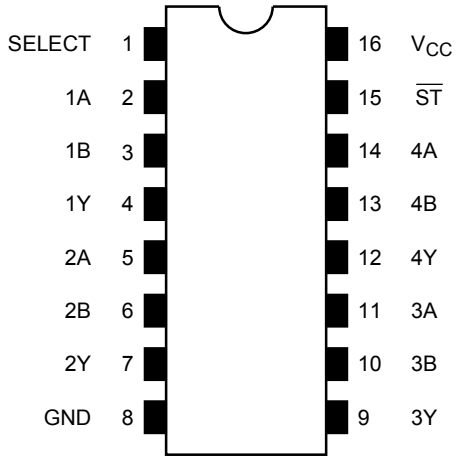
VSSOP16-P-0030-0.50

Weight: 0.02 g (typ.)

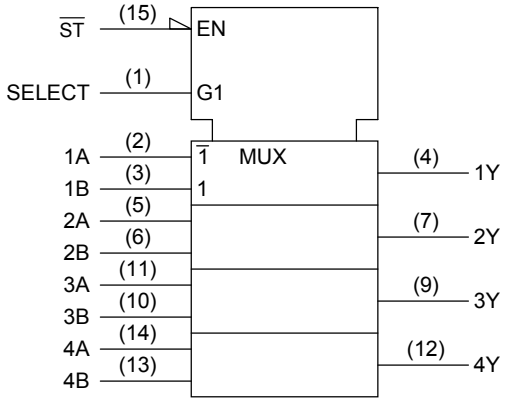
Features

- Low voltage operation: V_{CC} = 1.2~3.6 V
- High speed operation: t_{pd} = 3.0 ns (max) (V_{CC} = 3.0~3.6 V)
  t_{pd} = 3.5 ns (max) (V_{CC} = 2.3~2.7 V)
  t_{pd} = 7.0 ns (max) (V_{CC} = 1.65~1.95 V)
  t_{pd} = 14.0 ns (max) (V_{CC} = 1.4~1.6 V)
  t_{pd} = 35.0 ns (max) (V_{CC} = 1.2 V)
- 3.6 V tolerant inputs and outputs.
- Output current: I_{OH}/I_{OL} = ±24 mA (min) (V_{CC} = 3.0 V)
  I_{OH}/I_{OL} = ±18 mA (min) (V_{CC} = 2.3 V)
  I_{OH}/I_{OL} = ±6 mA (min) (V_{CC} = 1.65 V)
  I_{OH}/I_{OL} = ±2 mA (min) (V_{CC} = 1.4 V)
- Latch-up performance: ±300 mA
- ESD performance: Machine model > ±200 V
  Human body model > ±2000 V
- Package: VSSOP (US16)
- Power down protection is provided on all inputs and outputs.

Pin Assignment (top view)



IEC Logic Symbol

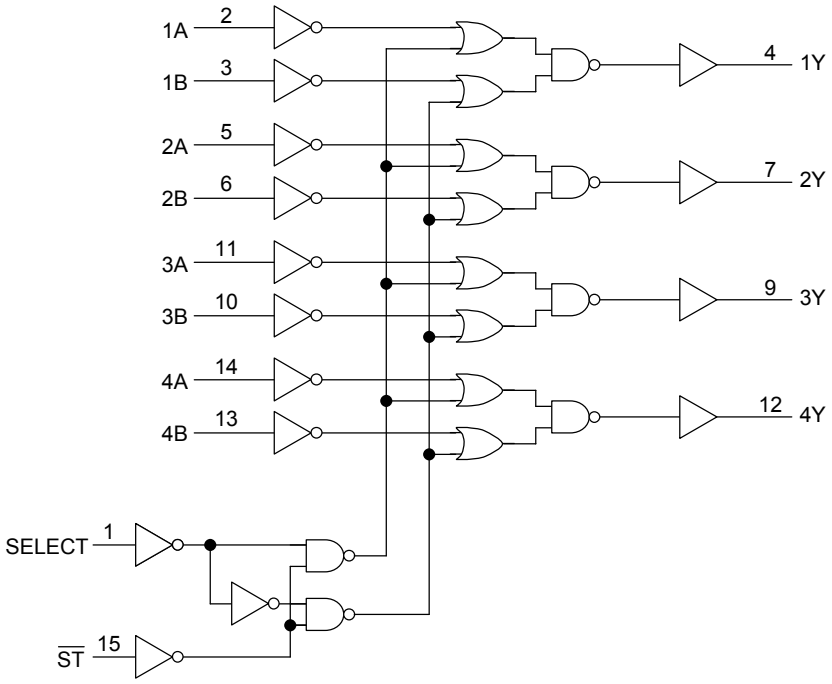


Truth Table

Inputs				Outputs
$\overline{ST}$	SELECT	A	B	Y
H	X	X	X	L
L	L	L	X	L
L	L	H	X	H
L	H	X	L	L
L	H	X	H	H

X: Don’t care

System Diagram



Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V_{CC}	−0.5~4.6	V
DC input voltage	V_{IN}	−0.5~4.6	V
DC output voltage	V_{OUT}	−0.5~4.6 (Note1)	V
		−0.5~V_{CC} + 0.5 (Note2)	
Input diode current	I_{IK}	−50	mA
Output diode current	I_{OK}	±50 (Note3)	mA
DC output current	I_{OUT}	±50	mA
Power dissipation	P_D	180	mW
DC V_{CC}/ground current	I_{CC}/I_{GND}	±100	mA
Storage temperature	T_{stg}	−65~150	°C

Note1: V_{CC} = 0 V

Note2: High or low state. I_{OUT} absolute maximum rating must be observed.

Note3: V_{OUT} < GND, V_{OUT} > V_{CC}

Recommended Operating Range

Characteristics	Symbol	Rating	Unit
Supply voltage	V_{CC}	1.2~3.6	V
Input voltage	V_{IN}	−0.3~3.6	V
Output voltage	V_{OUT}	0~3.6 (Note4)	V
		0~V_{CC} (Note5)	
Output current	I_{OH}/I_{OL}	±24 (Note6)	mA
		±18 (Note7)	
		±6 (Note8)	
		±2 (Note9)	
Operating temperature	T_{opr}	−40~85	°C
Input rise and fall time	dt/dv	0~10 (Note10)	ns/V

Note4: V_{CC} = 0 V

Note5: High or low state

Note6: V_{CC} = 3.0~3.6 V

Note7: V_{CC} = 2.3~2.7 V

Note8: V_{CC} = 1.65~1.95 V

Note9: V_{CC} = 1.4~1.6 V

Note10: V_{IN} = 0.8~2.0 V, V_{CC} = 3.0 V

Electrical Characteristics

DC Characteristics (Ta = −40~85°C, 2.7 V < V_{CC} ≦ 3.6 V)

Characteristics		Symbol	Test Condition		V_{CC} (V)	Min	Max	Unit
Input voltage	High level	V_{IH}	—		2.7~3.6	2.0	—	V
	Low level	V_{IL}	—		2.7~3.6	—	0.8	
Output voltage	High level	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −100 μA	2.7~3.6	V_{CC} − 0.2	—	V
				I_{OH} = −12 mA	2.7	2.2	—	
				I_{OH} = −18 mA	3.0	2.4	—	
				I_{OH} = −24 mA	3.0	2.2	—	
	Low level	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA	2.7~3.6	—	0.2	
				I_{OL} = 12 mA	2.7	—	0.4	
				I_{OL} = 18 mA	3.0	—	0.4	
				I_{OL} = 24 mA	3.0	—	0.55	
Input leakage current		I_{IN}	V_{IN} = 0~3.6 V		2.7~3.6	—	±5.0	μA
Power off leakage current		I_{OFF}	V_{IN}, V_{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent supply current		I_{CC}	V_{IN} = V_{CC} or GND		2.7~3.6	—	20.0	μA
			V_{CC} ≦ V_{IN} ≦ 3.6 V		2.7~3.6	—	±20.0	
Increase in I_{CC} per input		ΔI_{CC}	V_{IH} = V_{CC} − 0.6 V		2.7~3.6	—	750	

DC Characteristics (Ta = −40~85°C, 2.3 V ≦ V_{CC} ≦ 2.7 V)

Characteristics		Symbol	Test Condition		V_{CC} (V)	Min	Max	Unit
Input voltage	High level	V_{IH}	—		2.3~2.7	1.6	—	V
	Low level	V_{IL}	—		2.3~2.7	—	0.7	
Output voltage	High level	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −100 μA	2.3~2.7	V_{CC} − 0.2	—	V
				I_{OH} = −6 mA	2.3	2.0	—	
				I_{OH} = −12 mA	2.3	1.8	—	
				I_{OH} = −18 mA	2.3	1.7	—	
	Low level	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA	2.3~2.7	—	0.2	
				I_{OL} = 12 mA	2.3	—	0.4	
				I_{OL} = 18 mA	2.3	—	0.6	
Input leakage current		I_{IN}	V_{IN} = 0~3.6 V		2.3~2.7	—	±5.0	μA
Power off leakage current		I_{OFF}	V_{IN}, V_{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent supply current		I_{CC}	V_{IN} = V_{CC} or GND		2.3~2.7	—	20.0	μA
			V_{CC} ≦ V_{IN} ≦ 3.6 V		2.3~2.7	—	±20.0	

DC Characteristics (Ta = −40~85°C, 1.65 V ≦ V_{CC} < 2.3 V)

Characteristics		Symbol	Test Condition		V_{CC} (V)	Min	Max	Unit
Input voltage	High level	V_{IH}	—		1.65~2.3	0.65 × V_{CC}	—	V
	Low level	V_{IL}	—		1.65~2.3	—	0.2 × V_{CC}	
Output voltage	High level	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −100 μA	1.65~2.3	V_{CC} − 0.2	—	V
				I_{OH} = −6 mA	1.65	1.25	—	
	Low level	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA	1.65~2.3	—	0.2	
				I_{OL} = 6 mA	1.65	—	0.3	
Input leakage current		I_{IN}	V_{IN} = 0~3.6 V		1.65~2.3	—	±5.0	μA
Power off leakage current		I_{OFF}	V_{IN}, V_{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent supply current		I_{CC}	V_{IN} = V_{CC} or GND		1.65~2.3	—	20.0	μA
			V_{CC} ≦ V_{IN} ≦ 3.6 V		1.65~2.3	—	±20.0	

DC Characteristics (Ta = –40~85°C, 1.4 V ≦ V_{CC} ≦ 1.65 V)

Characteristics		Symbol	Test Condition		V_{CC} (V)	Min	Max	Unit
Input voltage	High level	V_{IH}	—		1.4~1.65	0.65 × V_{CC}	—	V
	Low level	V_{IL}	—		1.4~1.65	—	0.05 × V_{CC}	
Output voltage	High level	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = –100 μA	1.4~1.65	V_{CC} – 0.2	—	V
				I_{OH} = –2 mA	1.4	1.05	—	
	Low level	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA	1.4~1.65	—	0.05	
				I_{OL} = 2 mA	1.4	—	0.35	
Input leakage current		I_{IN}	V_{IN} = 0~3.6 V		1.4~1.65	—	±5.0	μA
Power off leakage current		I_{OFF}	V_{IN}, V_{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent supply current		I_{CC}	V_{IN} = V_{CC} or GND		1.4~1.65	—	20.0	μA
			V_{CC} ≦ V_{IN} ≦ 3.6 V		1.4~1.65	—	±20.0	

DC Characteristics (Ta = –40~85°C, 1.2 V ≦ V_{CC} < 1.4 V)

Characteristics		Symbol	Test Condition		V_{CC} (V)	Min	Max	Unit
Input voltage	High level	V_{IH}	—		1.2~1.4	0.8 × V_{CC}	—	V
	Low level	V_{IL}	—		1.2~1.4	—	0.05 × V_{CC}	
Output voltage	High level	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = –100 μA	1.2	V_{CC} – 0.1	—	V
	Low level	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA	1.2	—	0.05	
Input leakage current		I_{IN}	V_{IN} = 0~3.6 V		1.2	—	±5.0	μA
Power off leakage current		I_{OFF}	V_{IN}, V_{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent supply current		I_{CC}	V_{IN} = V_{CC} or GND		1.2	—	20.0	μA
			V_{CC} ≦ V_{IN} ≦ 3.6 V		1.2	—	±20.0	

AC Characteristics (Ta = –40~85°C, Input: $t_r = t_f = 2.0$ ns)

Characteristics	Symbol	Test Condition		V_{CC} (V)	Min	Max	Unit
Propagation delay time (A, B-Y)	t_{pLH} t_{pHL}	Figure 1, Figure 2	C_L = 15 pF, R_L = 2 kΩ	1.2	3.0	35.0	ns
				1.5 ± 0.1	2.0	14.0	
			C_L = 30 pF, R_L = 500 Ω	1.8 ± 0.15	1.5	7.0	
				2.5 ± 0.2	0.8	3.5	
				3.3 ± 0.3	0.6	3.0	
Propagation delay time (SELECT-Y)	t_{pLH} t_{pHL}	Figure 1, Figure 2	C_L = 15 pF, R_L = 2 kΩ	1.2	3.0	45.0	ns
				1.5 ± 0.1	2.0	18.0	
			C_L = 30 pF, R_L = 500 Ω	1.8 ± 0.15	1.5	9.0	
				2.5 ± 0.2	0.8	4.5	
				3.3 ± 0.3	0.6	3.5	
Propagation delay time ($\overline{ST}$ -Y)	t_{pLH} t_{pHL}	Figure 1, Figure 2	C_L = 15 pF, R_L = 2 kΩ	1.2	3.0	45.0	ns
				1.5 ± 0.1	2.0	18.0	
			C_L = 30 pF, R_L = 500 Ω	1.8 ± 0.15	1.5	9.0	
				2.5 ± 0.2	0.8	4.5	
				3.3 ± 0.3	0.6	3.5	
Output to output skew	t_{osLH} t_{osHL}	(Note11)	C_L = 15 pF, R_L = 2 kΩ	1.2	—	1.5	ns
				1.5 ± 0.1	—	1.5	
			C_L = 30 pF, R_L = 500 Ω	1.8 ± 0.15	—	0.5	
				2.5 ± 0.2	—	0.5	
				3.3 ± 0.3	—	0.5	

For C_L = 50 pF, add approximately 300 ps to the AC maximum specification.

Note11: This parameter is guaranteed by design.
($t_{osLH} = |t_{pLHm} - t_{pLHn}|$, $t_{osHL} = |t_{pHLm} - t_{pHLn}|$)

Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition	V_{CC} (V)	Typ.	Unit
Quiet output maximum dynamic V_{OL}	V_{OLP}	V_{IH} = 1.8 V, V_{IL} = 0 V (Note12)	1.8	0.25	V
		V_{IH} = 2.5 V, V_{IL} = 0 V (Note12)	2.5	0.6	
		V_{IH} = 3.3 V, V_{IL} = 0 V (Note12)	3.3	0.8	
Quiet output minimum dynamic V_{OL}	V_{OLV}	V_{IH} = 1.8 V, V_{IL} = 0 V (Note12)	1.8	−0.25	V
		V_{IH} = 2.5 V, V_{IL} = 0 V (Note12)	2.5	−0.6	
		V_{IH} = 3.3 V, V_{IL} = 0 V (Note12)	3.3	−0.8	
Quiet output minimum dynamic V_{OH}	V_{OHV}	V_{IH} = 1.8 V, V_{IL} = 0 V (Note12)	1.8	1.5	V
		V_{IH} = 2.5 V, V_{IL} = 0 V (Note12)	2.5	1.9	
		V_{IH} = 3.3 V, V_{IL} = 0 V (Note12)	3.3	2.2	

Note12: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

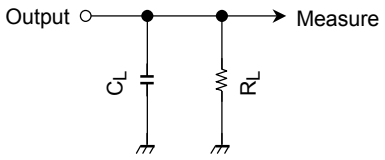
Characteristics	Symbol	Test Condition	V_{CC} (V)	Typ.	Unit
Input capacitance	C_{IN}	—	1.8, 2.5, 3.3	6	pF
Power dissipation capacitance	C_{PD}	f_{IN} = 10 MHz (Note13)	1.8, 2.5, 3.3	20	pF

Note13: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$I_{CC\ (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

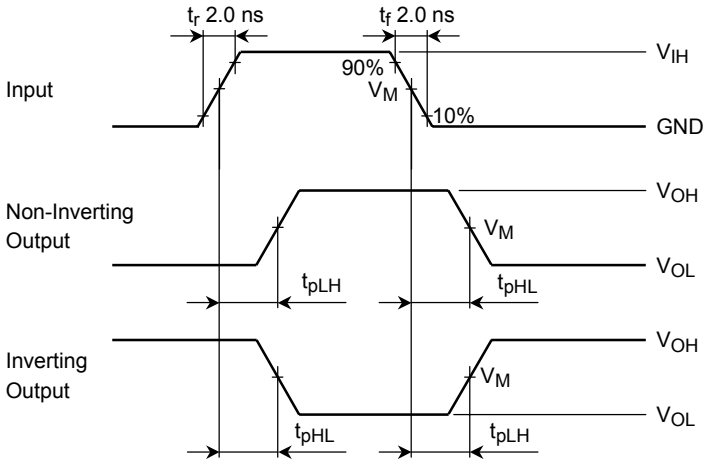
AC Test Circuit



Symbol	V_{CC}	
	3.3 ± 0.3 V 2.5 ± 0.2 V 1.8 ± 0.15 V	1.5 ± 0.1 V 1.2V
R_L	500 Ω	2 kΩ
C_L	30 pF	15 pF

Figure 1

AC Waveform

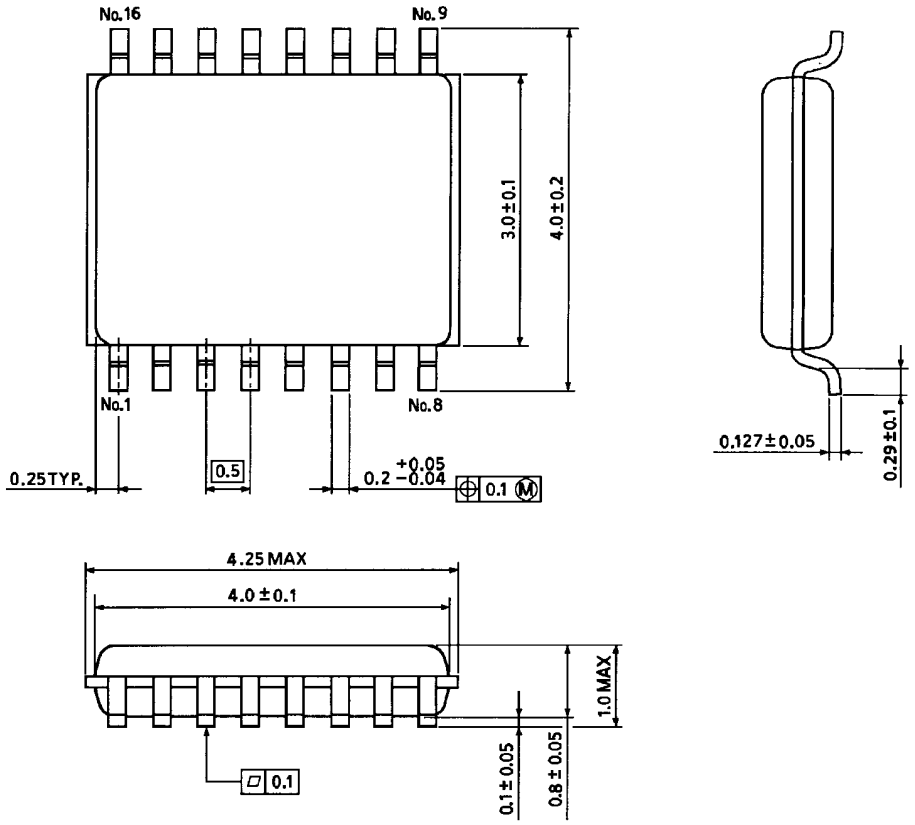


Symbol	V_{CC}				
	3.3 ± 0.3 V	2.5 ± 0.2 V	1.8 ± 0.15 V	1.5 ± 0.1 V	1.2 V
V_{IH}	2.7 V	V_{CC}	V_{CC}	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$

Figure 2 t_{pLH}, t_{pHL}

Package Dimensions

VSSOP16-P-0030-0.50 Unit : mm



Weight: 0.02 g (typ.)

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